

Schottky barrier diode

RB715F

●Applications

General purpose detection
High speed switching

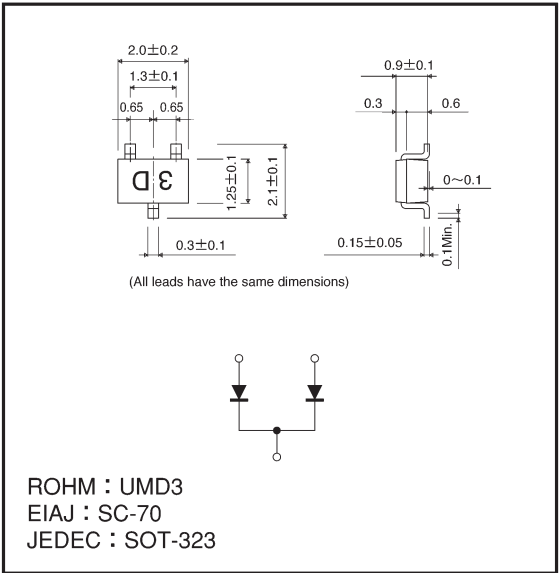
●Features

- 1) Multiple diodes with common cathode configuration.
- 2) High reliability.
- 3) Low reverse current and low forward voltage.

●Construction

Silicon epitaxial planar

●External dimensions (Units: mm)



●Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	40	V
DC reverse voltage	V_R	40	V
Mean rectifying current	I_O	30	mA
Peak forward surge current*	I_{FSM}	200	mA
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	-40~+125	°C

* 60 Hz for 1 ms

●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	—	0.28	0.37	V	$I_F=1\text{mA}$
Reverse current	I_R	—	0.05	1	μA	$V_R=10\text{V}$
Capacitance between terminals	C_T	—	2.0	—	pF	$V_R=1\text{V}$, $f=1\text{MHz}$

* ESD sensitive product handling required.

●Electrical characteristic curves ($T_a = 25^\circ\text{C}$ unless specified otherwise)

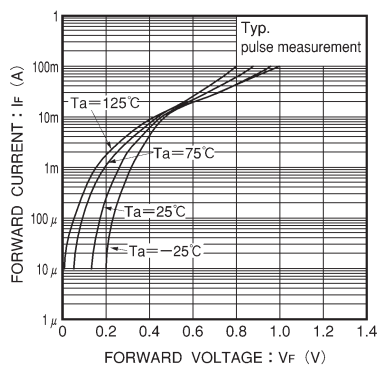


Fig. 1 Forward characteristics

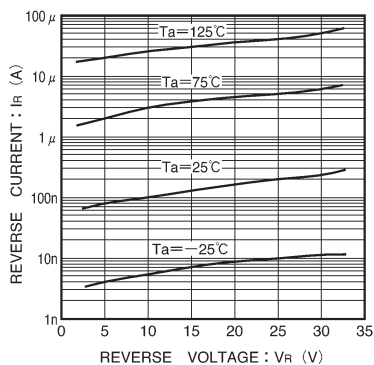


Fig. 2 Reverse characteristics

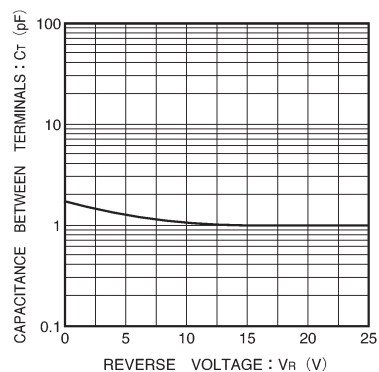


Fig. 3 Capacitance between terminals characteristics

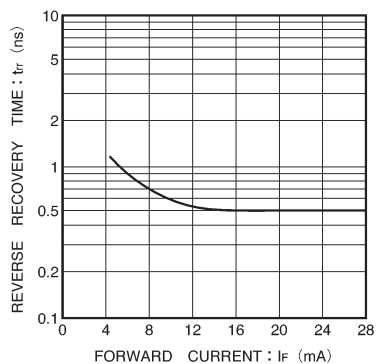


Fig. 4 Reverse recovery time characteristics

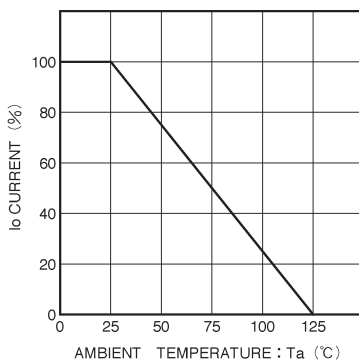


Fig. 5 Derating curve
(mounting on glass epoxy PCBs)